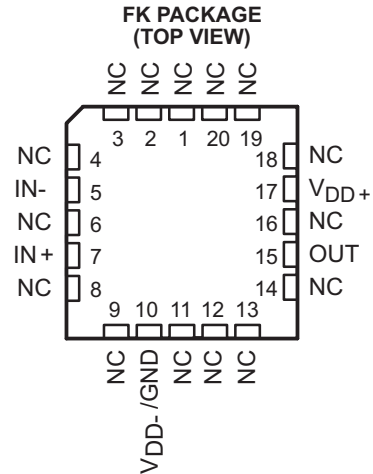


CLASS V, ADVANCED LinCMOS™ LOW NOISE PRECISION OPERATIONAL AMPLIFIER

Check for Samples: [TLC2201-SP](#)

FEATURES

- QML-V Qualified SMD 5962-9088203V2A
- Low Input Offset Voltage: 400 μV Max
- Excellent Offset Voltage Stability With Temperature: 0.5 $\mu\text{V}/^\circ\text{C}$ Typ
- Rail-to-Rail Output Swing
- Low Input Bias Current: 1 pA Typ at $T_A = 25^\circ\text{C}$
- Common-Mode Input Voltage Range Includes the Negative Rail
- Fully Specified For Both Single-Supply and Split-Supply Operation



NC - No internal connection

DESCRIPTION

The TLC2201 is a precision, low-noise operational amplifier using Texas Instruments Advanced LinCMOS™ process. This device combines the noise performance of the lowest-noise JFET amplifiers with the dc precision available previously only in bipolar amplifiers. The Advanced LinCMOS™ process uses silicon-gate technology to obtain input offset voltage stability with temperature and time that far exceeds that obtainable using metal-gate technology. In addition, this technology makes possible input impedance levels that meet or exceed levels offered by top-gate JFET and expensive dielectric-isolated devices.

The combination of excellent DC and noise performance with a common-mode input voltage range that includes the negative rail makes these devices an ideal choice for high-impedance, low-level signal-conditioning applications in either single-supply or split-supply configurations.

The device inputs and outputs are designed to withstand -100-mA surge currents without sustaining latch-up. In addition, internal ESD-protection circuits prevent functional failures at voltages up to 2000 V as tested under MIL-PRF-38535, Method 3015.2; however, care should be exercised in handling these devices as exposure to ESD may result in degradation of the parametric performance.

The TLC2201 is characterized for operation over the full military temperature range of -55°C to 125°C .



Please be aware that an important notice concerning availability, standard warranty, and use in critical applications of Texas Instruments semiconductor products and disclaimers thereto appears at the end of this data sheet.

LinCMOS is a trademark of Texas Instruments.

Parts, PSpice are trademarks of MicroSim Corporation.

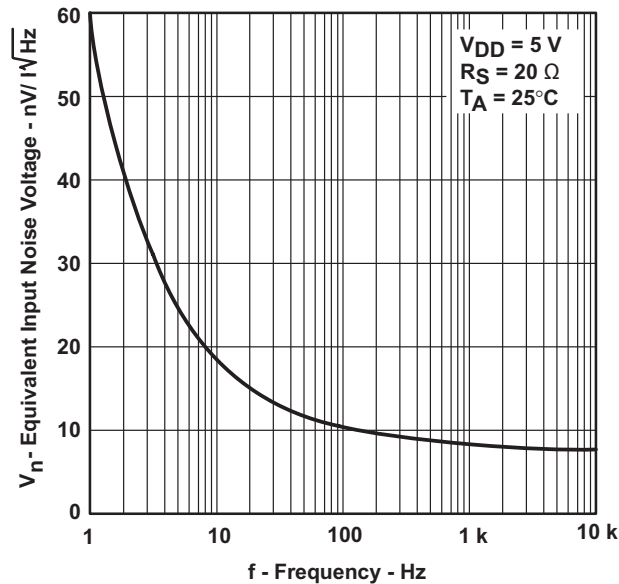
PRODUCTION DATA information is current as of publication date. Products conform to specifications per the terms of the Texas Instruments standard warranty. Production processing does not necessarily include testing of all parameters.



This integrated circuit can be damaged by ESD. Texas Instruments recommends that all integrated circuits be handled with appropriate precautions. Failure to observe proper handling and installation procedures can cause damage.

ESD damage can range from subtle performance degradation to complete device failure. Precision integrated circuits may be more susceptible to damage because very small parametric changes could cause the device not to meet its published specifications.

**TYPICAL EQUIVALENT
INPUT NOISE VOLTAGE
vs
FREQUENCY**

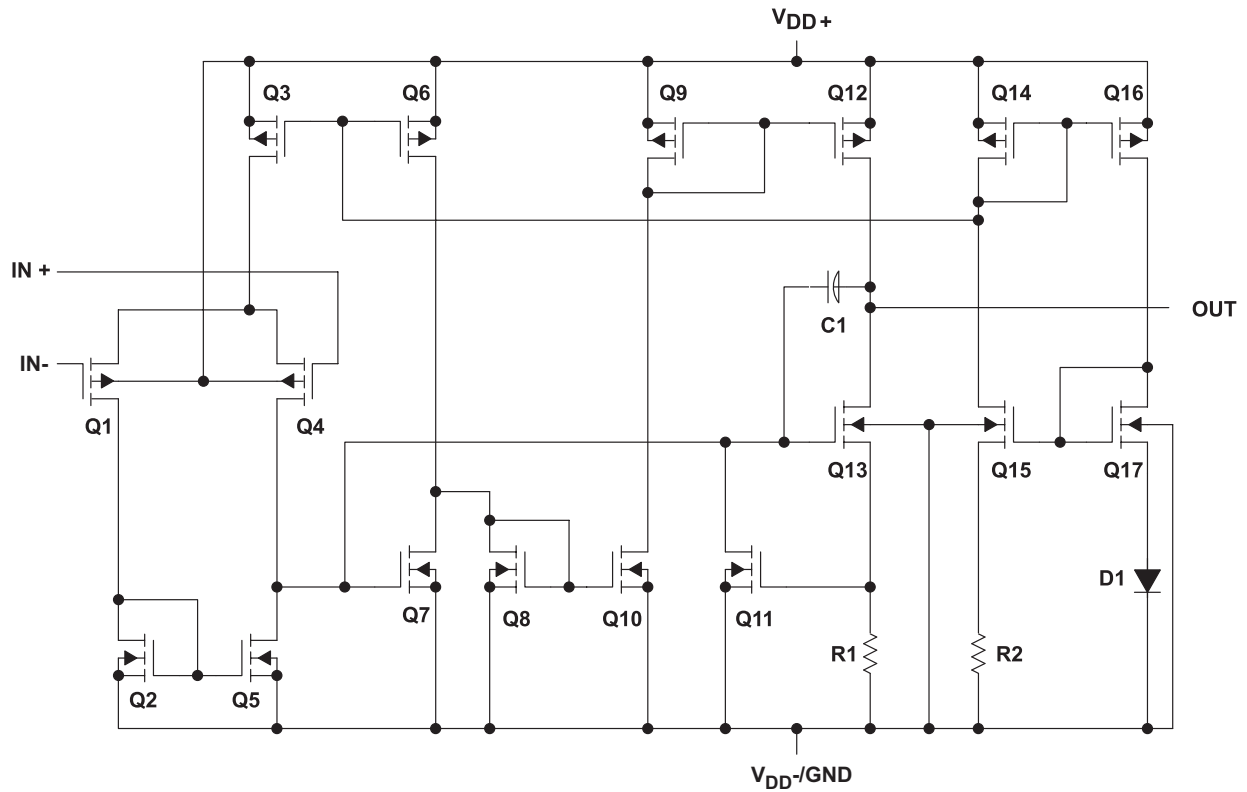


ORDERING INFORMATION⁽¹⁾

| TEMPERATURE | PACKAGE ⁽²⁾ | ORDERABLE PART NUMBER | TOP-SIDE MARKING |
|----------------------------------|------------------------|-----------------------|-------------------------------------|
| -55°C to 125°C T _{case} | 20-pin FK | 5962-9088203V2A | 5962-9088203V2A TLC2201AMFKBQMLV |

- (1) For the most current package and ordering information, see the Package Option Addendum at the end of this document, or see the TI web site at www.ti.com.
- (2) Package drawings, thermal data, and symbolization are available at www.ti.com/packaging.

EQUIVALENT SCHEMATIC



| ACTUAL DEVICE COMPONENT COUNT | |
|-------------------------------|---------|
| COMPONENT | TLC2201 |
| Transistors | 17 |
| Resistors | 2 |
| Diodes | 1 |
| Capacitors | 1 |

ABSOLUTE MAXIMUM RATINGS⁽¹⁾

Over operating free-air temperature range (unless otherwise noted).

| | | VALUE | UNIT |
|------------------|--|-------------------------------|------|
| V _{DD} | Supply voltage ⁽²⁾ , V _{DD-} to V _{DD+} | -8 to 8 | V |
| V _{ID} | Differential input voltage ⁽³⁾ | ±16 | V |
| V _I | Input voltage (any input) | ±8 | V |
| I _I | Input current (each input) | ±5 | mA |
| I _O | Output current (each output) | ±50 | mA |
| | Duration of short-circuit current at (or below) 25°C ⁽⁴⁾ | Unlimited | |
| | Continuous total power dissipation | See Dissipation Ratings Table | |
| T _C | Operating case temperature | -55 to 125 | °C |
| T _{stg} | Storage temperature | -65 to 150 | °C |
| | Case temperature for 60 seconds | 260 | °C |

- (1) Stresses beyond those listed under *absolute maximum ratings* may cause permanent damage to the device. These are stress ratings only and functional operation of the device at these or any other conditions beyond those indicated under *recommended operating conditions* is not implied. Exposure to absolute-maximum-rated conditions for extended periods may affect device reliability.
- (2) All voltage values except differential voltages are with respect to the midpoint between V_{DD+} and V_{DD-}.
- (3) Differential voltages are at IN+ with respect to IN-.
- (4) The output may be shorted to either supply. Temperature and/or supply voltages must be limited to ensure that the maximum dissipation rating is not exceeded.

THERMAL RESISTANCE FOR FK PACKAGE⁽¹⁾⁽²⁾

over operating free-air temperature range (unless otherwise noted)

| PARAMETER | | TEST CONDITIONS | MIN | TYP | MAX | UNIT |
|------------------|-------------------------------------|------------------------------|-----|-----|-----|------|
| R _{θJC} | Junction-to-case thermal resistance | MIL-STD-883 test method 1012 | | | 16 | °C/W |

- (1) Maximum power dissipation is a function of T_J (max), θ_{JC} and T_C. The maximum allowable power dissipation at any allowable case temperature is PD = (T_J (max) - T_C)/θ_{JC}. Operating at the absolute maximum T_J of 150°C can affect reliability.
- (2) The package thermal impedance is calculated in accordance with MIL-STD-883.

RECOMMENDED OPERATING CONDITIONS

| | | MIN | MAX | UNIT |
|------------------|----------------------------|------------------|-----------------------|------|
| V _{DD±} | Supply voltage | ±2.3 | ±8 | V |
| V _{IC} | Common-mode input voltage | V _{DD-} | V _{DD+} -2.3 | V |
| T _C | Operating case temperature | -55 | 125 | °C |

ELECTRICAL CHARACTERISTICS

over operating free-air temperature range, $V_{DD} = 5\text{ V}$ (unless otherwise noted)

| PARAMETER | | TEST CONDITIONS | $T_A^{(1)}$ | MIN | TYP | MAX | UNIT | | |
|----------------|---|--|---|-----------------------------------|--|------------|------------------------------|---------------|------------------------------|
| V_{IO} | Input offset voltage | $V_{IC} = 0,$ $R_S = 50\ \Omega$ | 25°C | | 80 | 200 | μV | | |
| | | | Full range | | | 400 | | | |
| α_{VIO} | Temperature coefficient of input offset voltage | | Full range | | 0.5 | | $\mu\text{V}/^\circ\text{C}$ | | |
| | Input offset voltage long-term drift ⁽²⁾ | | 25°C | | 0.001 | | $\mu\text{V}/\text{mo}$ | | |
| I_{IO} | Input offset current | | 25°C | | 0.5 | | pA | | |
| | | | Full range | | | 500 | | | |
| I_{IB} | Input bias current | | 25°C | | 1 | | pA | | |
| | | | Full range | | | 500 | | | |
| V_{ICR} | Common-mode input voltage range | $R_S = 50\ \Omega$ | Full range | 0 to 2.7 | | | V | | |
| V_{OH} | Maximum high-level output voltage | $R_L = 10\ \text{k}\Omega$ | 25°C | 4.7 | 4.8 | | V | | |
| | | | Full range | 4.7 | | | | | |
| V_{OL} | Maximum low-level output voltage | | $I_O = 0$ | 25°C | 0 | 50 | mV | | |
| | | | Full range | | | 50 | | | |
| A_{VD} | Large-signal differential voltage amplification | | $V_O = 1\ \text{V to } 4\ \text{V},$ $R_L = 500\ \text{k}\Omega$ | 25°C | 150 | 315 | V/mV | | |
| | | | | Full range | 75 | | | | |
| | | | | 25°C | $V_O = 1\ \text{V to } 4\ \text{V},$ $R_L = 10\ \text{k}\Omega$ | 25 | | 55 | |
| | | | | | | Full range | | 10 | |
| CMRR | Common-mode rejection ratio | $V_{IC} = V_{ICRmin},$ $V_O = 0,$ $R_S = 50\ \Omega$ | 25°C | 90 | 110 | dB | | | |
| | | | Full range | 85 | | | | | |
| k_{SVR} | Supply voltage rejection ratio ($\Delta V_{DD\pm}/\Delta V_{IO}$) | | $V_{DD} = 4.6\ \text{V to } 16\ \text{V}$ | 25°C | 90 | 110 | dB | | |
| | | | | Full range | 85 | | | | |
| I_{DD} | Supply current | | | $V_O = 2.5\ \text{V},$ No load | 25°C | | 1.1 | 1.5 | mA |
| | | | | | Full range | | | 1.5 | |
| SR | Slew rate at unity gain | | | | $V_O = 0.5\ \text{V to } 2.5\ \text{V},$ $R_L = 10\ \text{k}\Omega$ $C_L = 100\ \text{pF}$ | 25°C | 1.8 | 2.5 | V/ μs |
| | | | | | | Full range | 1.1 | | |
| V_n | Equivalent input noise voltage | f = 10 Hz | | | | 25°C | | 18 | $\text{nV}/\sqrt{\text{Hz}}$ |
| | | f = 1 kHz | | | | 25°C | | 8 | |
| $V_{n(pp)}$ | Peak-to-peak equivalent input noise voltage | f = 0.1 to 1 Hz | 25°C | | | | 0.5 | μV | |
| | | f = 0.1 to 10 Hz | 25°C | | | | 0.7 | | |
| I_n | Equivalent input noise current | | 25°C | | | 0.6 | $\text{fA}/\sqrt{\text{Hz}}$ | | |
| | Gain-bandwidth product | f = 10 kHz, $R_L = 10\ \text{k}\Omega,$ $C_L = 100\ \text{pF}$ | 25°C | | | 1.8 | MHz | | |
| Φ_m | Phase margin at unity gain | $R_L = 10\ \text{k}\Omega,$ $C_L = 100\ \text{pF}$ | 25°C | | 45° | | | | |

(1) Full range is -55°C to 125°C .

(2) Typical values are based on the input offset voltage shift observable through 168 hours of operating life test at $T_A = 150^\circ\text{C}$ extrapolated to $T_A = 25^\circ\text{C}$ using the Arrhenius equation and assuming an activation energy of 0.96 eV.

ELECTRICAL CHARACTERISTICS

over operating free-air temperature range, $V_{DD} = \pm 5$ V (unless otherwise noted)

| PARAMETER | | TEST CONDITIONS | $T_A^{(1)}$ | MIN | TYP | MAX | UNIT |
|----------------|---|--|-------------|-----------|-------|---------|------------------|
| V_{IO} | Input offset voltage | $V_{IC} = 0$, $R_S = 50 \Omega$ | 25°C | | 80 | 200 | μV |
| | | | Full range | | | 400 | |
| α_{VIO} | Temperature coefficient of input offset voltage | | Full range | | 0.5 | | $\mu V/^\circ C$ |
| | Input offset voltage long-term drift ⁽²⁾ | | 25°C | | 0.001 | | $\mu V/mo$ |
| I_{IO} | Input offset current | | 25°C | | 0.5 | | μA |
| | | | Full range | | | 500 | |
| I_{IB} | Input bias current | 25°C | | 1 | | μA | |
| | | Full range | | | 500 | | |
| V_{ICR} | Common-mode input voltage range | $R_S = 50 \Omega$ | Full range | -5 to 2.7 | | | V |
| V_{OM+} | Maximum positive peak output voltage swing | $R_L = 10 k\Omega$ | 25°C | 4.7 | 4.8 | | V |
| | | | Full range | 4.7 | | | |
| V_{OM-} | Maximum negative peak output voltage swing | | 25°C | -4.7 | -4.9 | | V |
| | | | Full range | -4.7 | | | |
| A_{VD} | Large-signal differential voltage amplification | $V_O = \pm 4$ V, $R_L = 500 k\Omega$ | 25°C | 400 | 560 | | V/mV |
| | | | Full range | 200 | | | |
| | | $V_O = \pm 4$ V, $R_L = 10 k\Omega$ | 25°C | 90 | 100 | | |
| | | | Full range | 45 | | | |
| CMRR | Common-mode rejection ratio | $V_{IC} = V_{ICRmin}$, $V_O = 0$, $R_S = 50 \Omega$ | 25°C | 90 | 115 | | dB |
| | | | Full range | 85 | | | |
| k_{SVR} | Supply voltage rejection ratio ($\Delta V_{DD\pm}/\Delta V_{IO}$) | $V_{DD} = \pm 2.3$ V to ± 8 V | 25°C | 90 | 110 | | dB |
| | | | Full range | 85 | | | |
| I_{DD} | Supply current | $V_O = 0$ V, No load | 25°C | | 1.1 | 1.5 | mA |
| | | | Full range | | | 1.5 | |
| SR | Slew rate at unity gain | $V_O = \pm 2.3$ V, $R_L = 10 k\Omega$, $C_L = 100$ pF | 25°C | 2 | 2.7 | | V/ μs |
| | | | Full range | 1.3 | | | |
| V_n | Equivalent input noise voltage | f = 10 Hz | 25°C | | 18 | | nV/ \sqrt{Hz} |
| | | f = 1 kHz | 25°C | | 8 | | |
| $V_{n(pp)}$ | Peak-to-peak equivalent input noise voltage | f = 0.1 to 1 Hz | 25°C | | 0.5 | | μV |
| | | f = 0.1 to 10 Hz | 25°C | | 0.7 | | |
| I_n | Equivalent input noise current | | 25°C | | 0.6 | | fA/ \sqrt{Hz} |
| | Gain-bandwidth product | f = 10 kHz, $R_L = 10 k\Omega$, $C_L = 100$ pF | 25°C | | 1.9 | | MHz |
| Φ_m | Phase margin at unity gain | $R_L = 10 k\Omega$, $C_L = 100$ pF | 25°C | | 48° | | |

(1) Full range is $-55^\circ C$ to $125^\circ C$.

(2) Typical values are based on the input offset voltage shift observable through 168 hours of operating life test at $T_A = 150^\circ C$ extrapolated to $T_A = 25^\circ C$ using the Arrhenius equation and assuming an activation energy of 0.96 eV.

PARAMETER MEASUREMENT INFORMATION

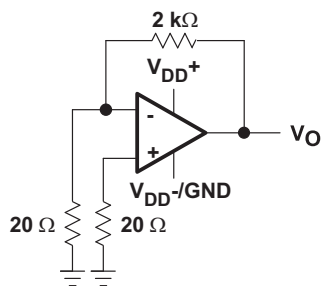
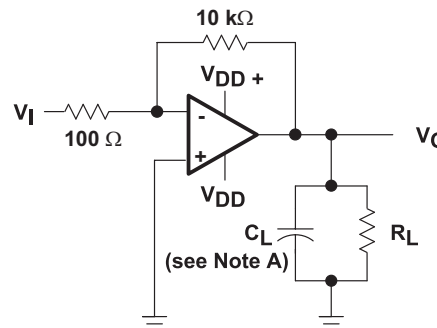
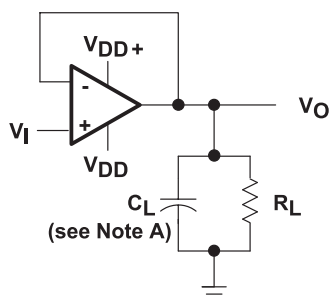


Figure 1. Noise-Voltage Test Circuit



NOTE A: C_L includes fixture capacitance.

Figure 2. Phase-Margin Test Circuit



NOTE A: C_L includes fixture capacitance.

Figure 3. Slew-Rate Test Circuit

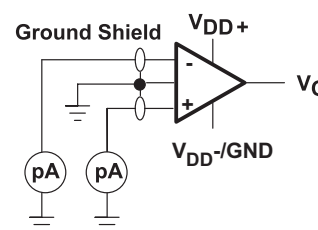


Figure 4. Input-Bias and Offset-Current Test Circuit

TYPICAL VALUES

Typical values presented in this data sheet represent the median (50% point) of device parametric performance.

INPUT BIAS AND OFFSET CURRENT

At the picoamp bias current level of the TLC2201 accurate measurement of the bias current becomes difficult. Not only does this measurement require a picoammeter, but test socket leakages can easily exceed the actual device bias currents. To measure these small currents, Texas Instruments uses a two-step process. The socket leakage is measured using picoammeters with bias voltages applied but with no device in the socket. The device is then inserted in the socket, and a second test measuring both the socket leakage and the device input bias current is performed. The two measurements are then subtracted algebraically to determine the bias current of the device.

NOISE

Texas Instruments offers automated production noise testing to meet individual application requirements. Noise voltage at $f = 10$ Hz and $f = 1$ kHz is sample tested on every TLC2201. For other noise requirements, please contact the factory.

TYPICAL CHARACTERISTICS

Table of Graphs

| | | | FIGURE |
|-------------|---|------------------------------|---------------------------|
| V_{IO} | Input offset voltage | Distribution | Figure 5 |
| I_{IB} | Input bias current | vs Common-mode input voltage | Figure 6 |
| | | vs Free-air temperature | Figure 7 |
| V_{OM} | Maximum peak output voltage | vs Output curre | Figure 8 |
| | | vs Free-air temperature | Figure 9 |
| $V_{O(PP)}$ | Maximum peak-to-peak output voltage | vs Frequency | Figure 10 |
| V_{OH} | High-level output voltage | vs Frequency | Figure 11 |
| | | vs High-level output current | Figure 12 |
| | | vs Free-air temperature | Figure 13 |
| V_{OL} | Low-level output voltage | vs Low-level output current | Figure 14 |
| | | vs Free-air temperature | Figure 15 |
| A_{VD} | Large-signal differential voltage amplification | vs Frequency | Figure 16 |
| | | vs Free-air temperature | Figure 17 |
| I_{OS} | Short-circuit output current | vs Supply voltage | Figure 18 |
| | | vs Free-air temperature | Figure 19 |
| CMRR | Common-mode rejection ratio | vs Frequency | Figure 20 |
| I_{DD} | Supply current | vs Supply voltage | Figure 21 |
| | | vs Free-air temperature | Figure 22 |
| | Pulse response | Small signal | Figure 23 |
| | | | Figure 24 |
| | | Large signal | Figure 25 |
| | | | Figure 26 |
| SR | Slew rate | vs Supply voltage | Figure 27 |
| | | vs Free-air temperature | Figure 28 |
| | Noise voltage (referred to input) | 0.1 Hz to 1 Hz | Figure 29 |
| | | 0.1 Hz to 10 Hz | Figure 30 |
| | Gain-bandwidth product | vs Supply voltage | Figure 31 |
| | | vs Free-air temperature | Figure 32 |
| Φ_m | Phase margin | vs Supply voltage | Figure 33 |
| | | vs Free-air temperature | Figure 34 |
| | Phase shift | vs Frequency | Figure 16 |

TYPICAL CHARACTERISTICS

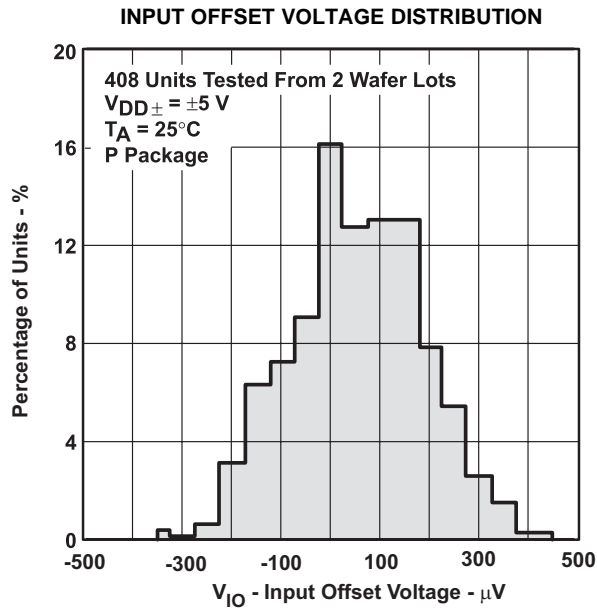


Figure 5.

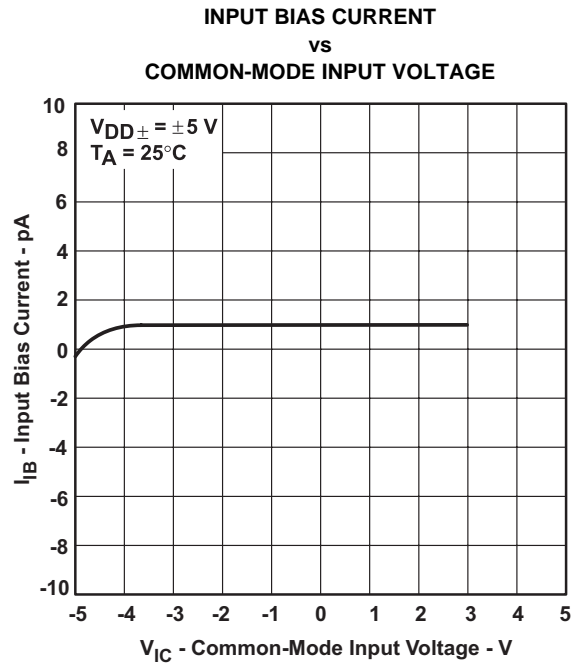


Figure 6.

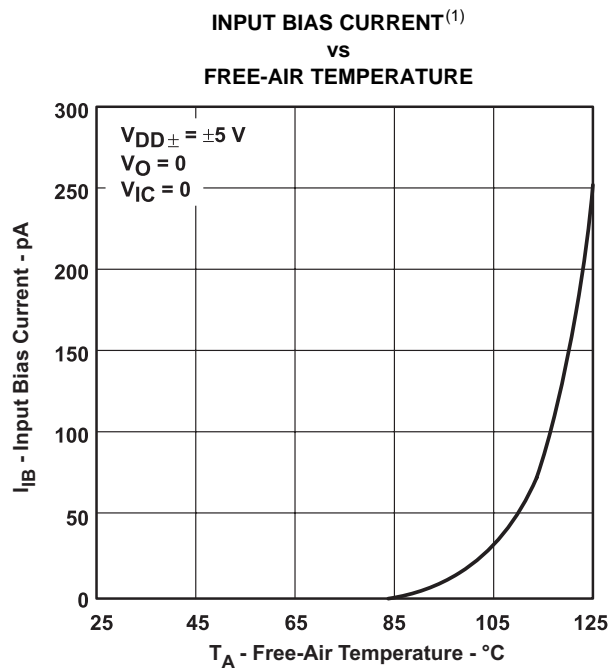


Figure 7.

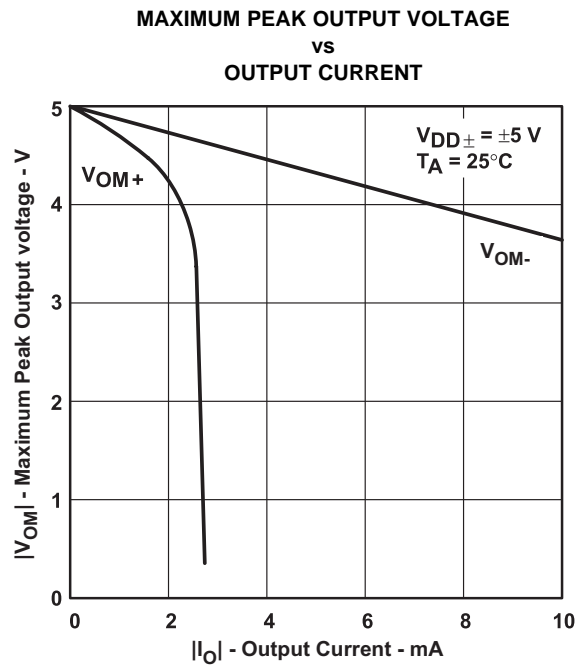


Figure 8.

(1) Data at high and low temperatures are applicable only within the rated operating free-air temperature ranges of the various devices.

TYPICAL CHARACTERISTICS (continued)

**MAXIMUM PEAK OUTPUT VOLTAGE⁽²⁾
vs
FREE-AIR TEMPERATURE**

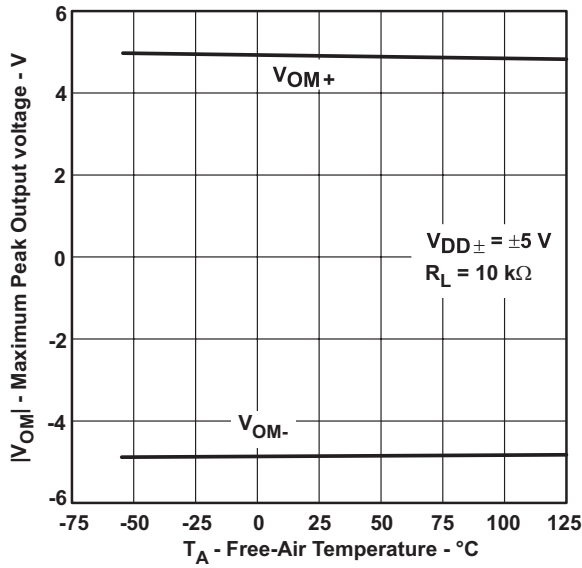


Figure 9.

**MAXIMUM PEAK-TO-PEAK OUTPUT VOLTAGE
vs
FREQUENCY**

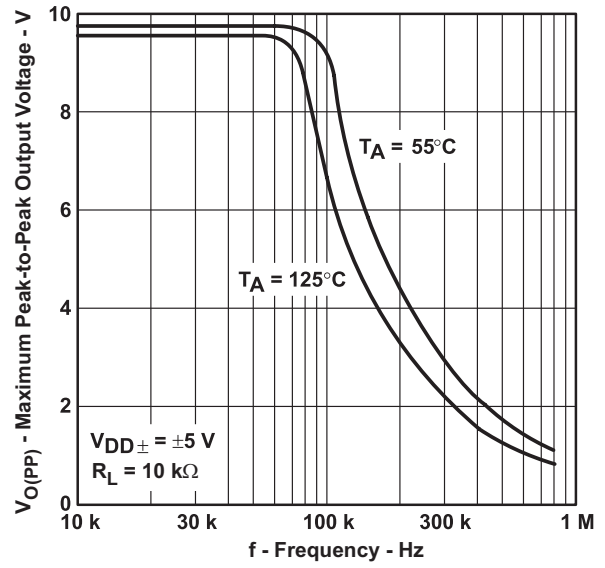


Figure 10.

**HIGH-LEVEL OUTPUT VOLTAGE
vs
FREQUENCY**

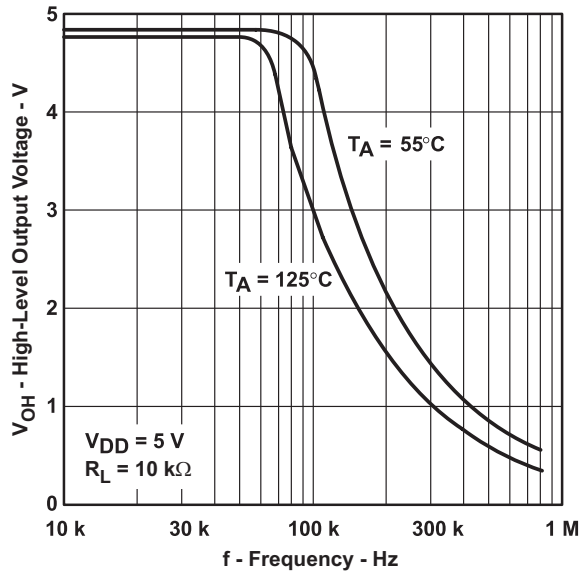


Figure 11.

**HIGH-LEVEL OUTPUT VOLTAGE
vs
HIGH-LEVEL OUTPUT CURRENT**

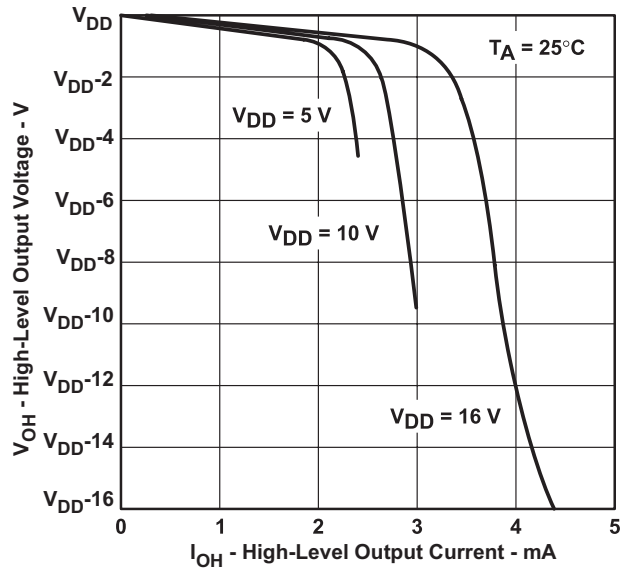


Figure 12.

(2) Data at high and low temperatures are applicable only within the rated operating free-air temperature ranges of the various devices.

TYPICAL CHARACTERISTICS (continued)

HIGH-LEVEL OUTPUT VOLTAGE vs FREE-AIR TEMPERATURE

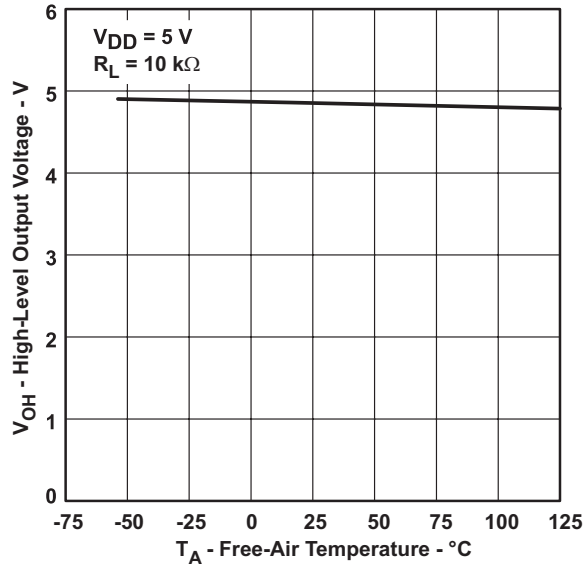


Figure 13.

LOW-LEVEL OUTPUT VOLTAGE vs LOW-LEVEL OUTPUT CURRENT

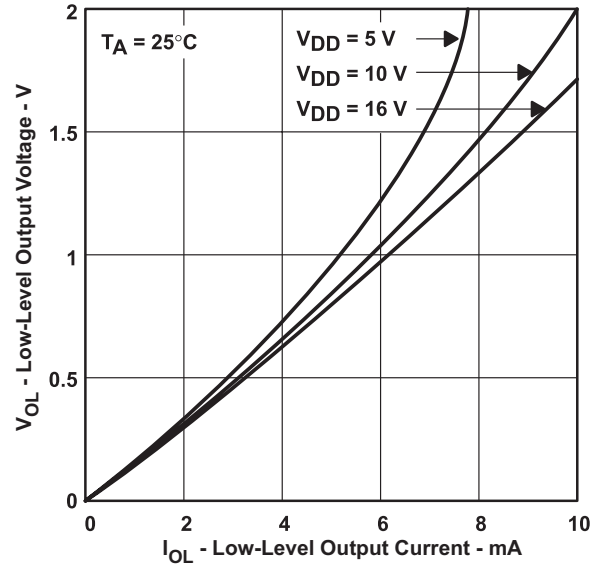


Figure 14.

LOW-LEVEL OUTPUT VOLTAGE vs FREE-AIR TEMPERATURE

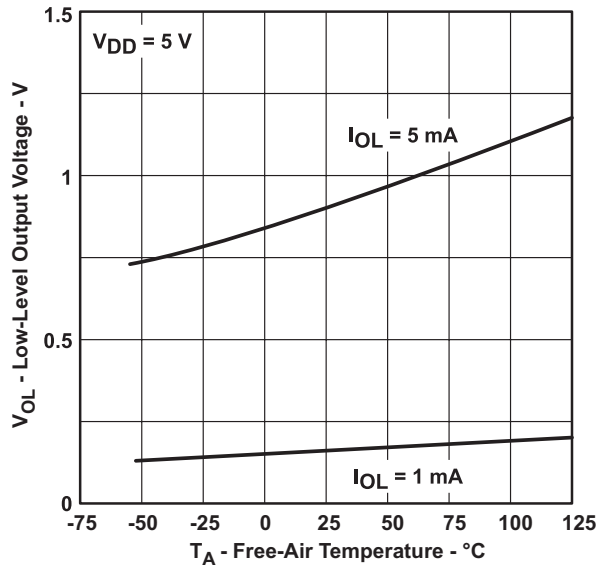


Figure 15.

LARGE-SIGNAL DIFFERENTIAL VOLTAGE AMPLIFICATION AND PHASE SHIFT vs FREQUENCY

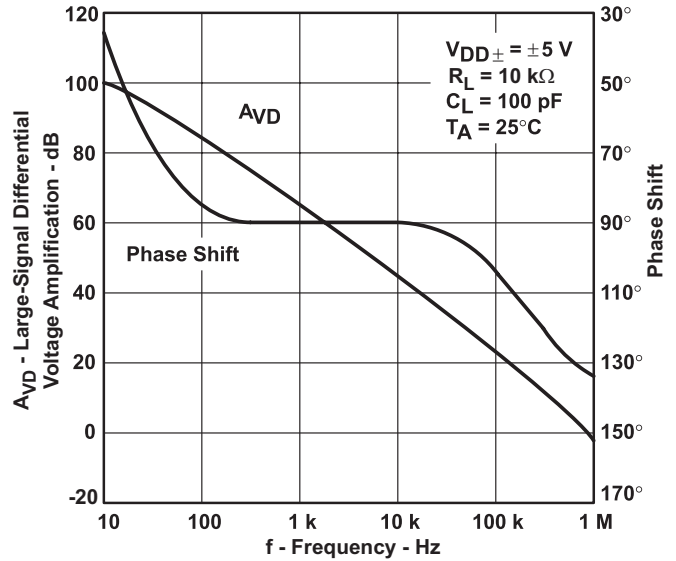


Figure 16.

TYPICAL CHARACTERISTICS (continued)

LARGE-SIGNAL DIFFERENTIAL VOLTAGE AMPLIFICATION

vs
FREE-AIR TEMPERATURE

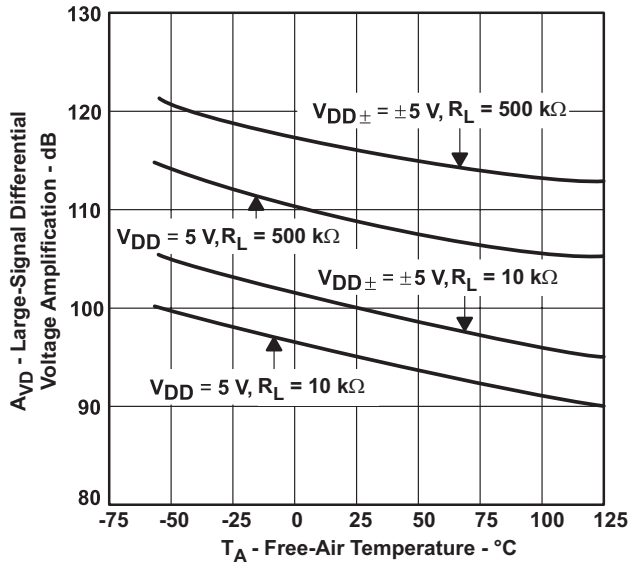


Figure 17.

SHORT-CIRCUIT OUTPUT CURRENT

vs
SUPPLY VOLTAGE

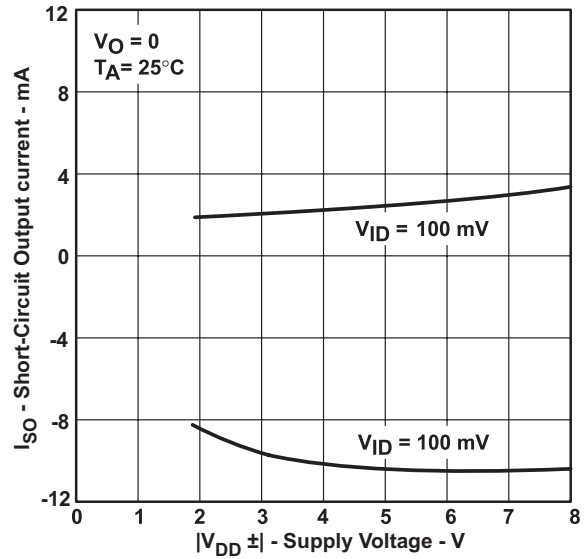


Figure 18.

SHORT-CIRCUIT OUTPUT CURRENT

vs
FREE-AIR TEMPERATURE

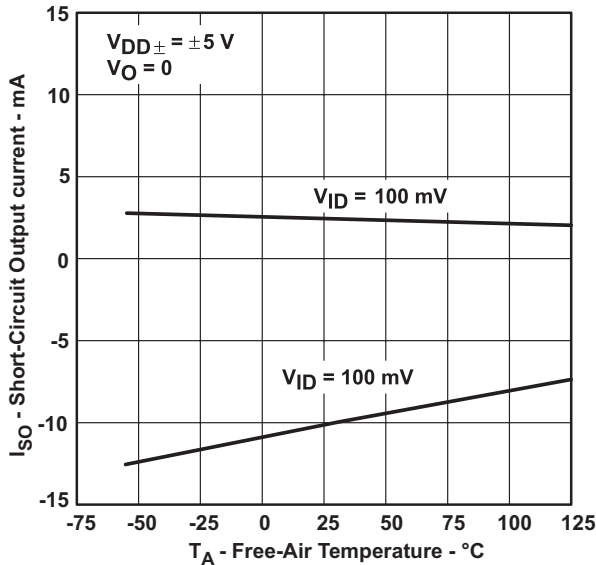


Figure 19.

COMMON-MODE REJECTION RATIO

vs
FREQUENCY

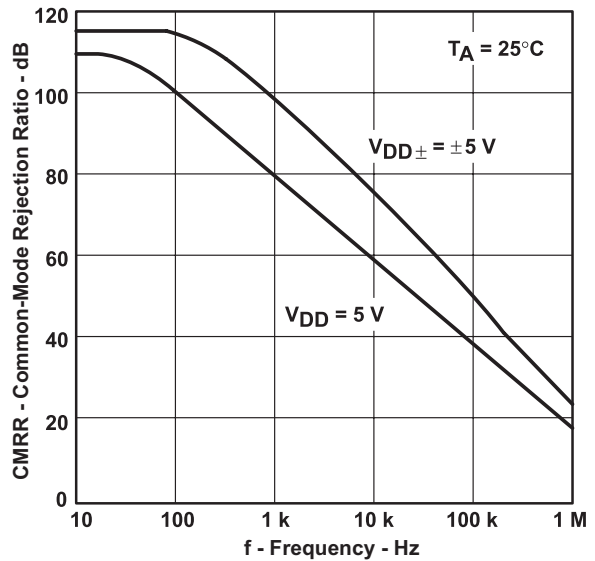


Figure 20.

TYPICAL CHARACTERISTICS (continued)

SUPPLY CURRENT
vs
SUPPLY VOLTAGE

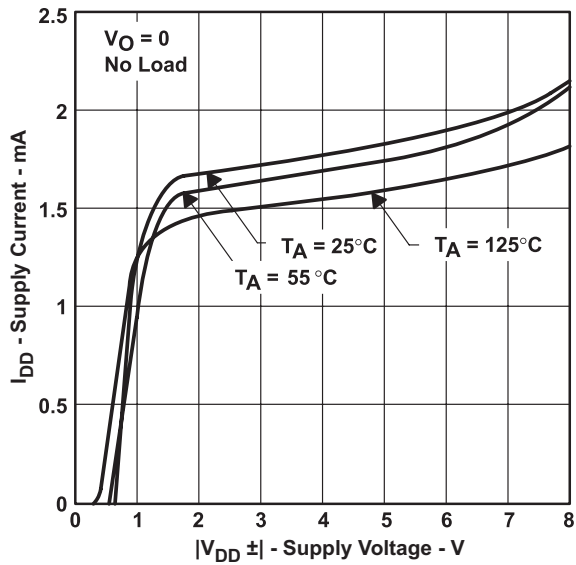


Figure 21.

SUPPLY CURRENT
vs
FREE-AIR TEMPERATURE

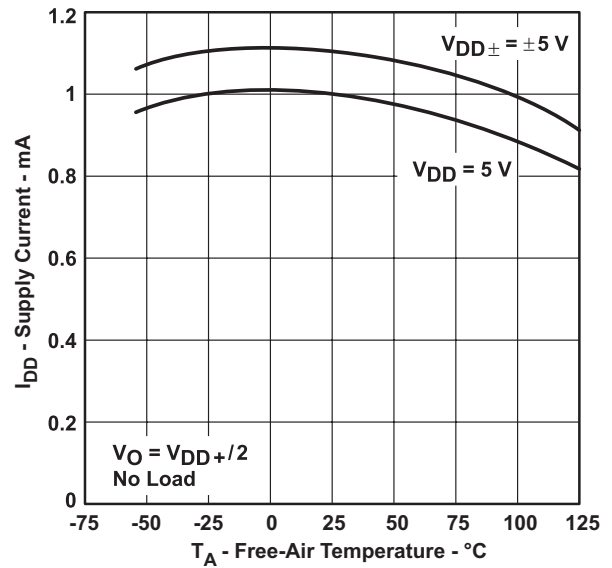


Figure 22.

VOLTAGE-FOLLOWER
SMALL-SIGNAL
PULSE RESPONSE

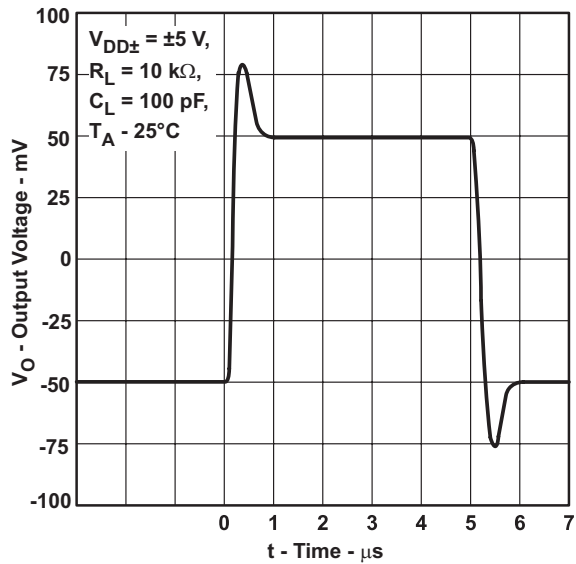


Figure 23.

VOLTAGE-FOLLOWER
SMALL-SIGNAL
PULSE RESPONSE

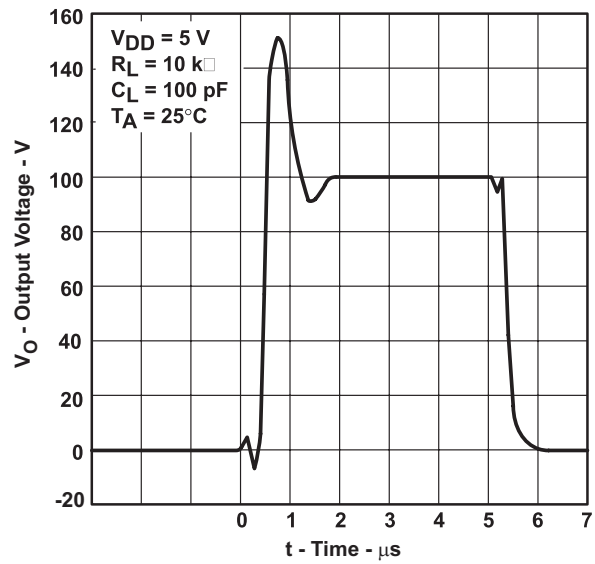


Figure 24.

TYPICAL CHARACTERISTICS (continued)

**VOLTAGE-FOLLOWER
LARGE-SIGNAL
PULSE RESPONSE**

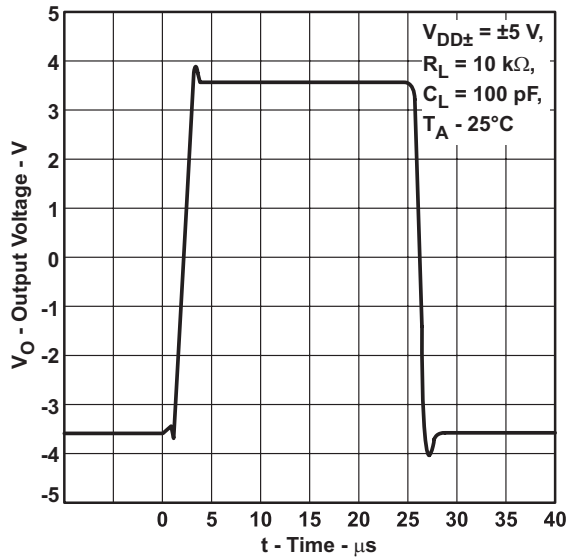


Figure 25.

**VOLTAGE-FOLLOWER
LARGE-SIGNAL
PULSE RESPONSE**

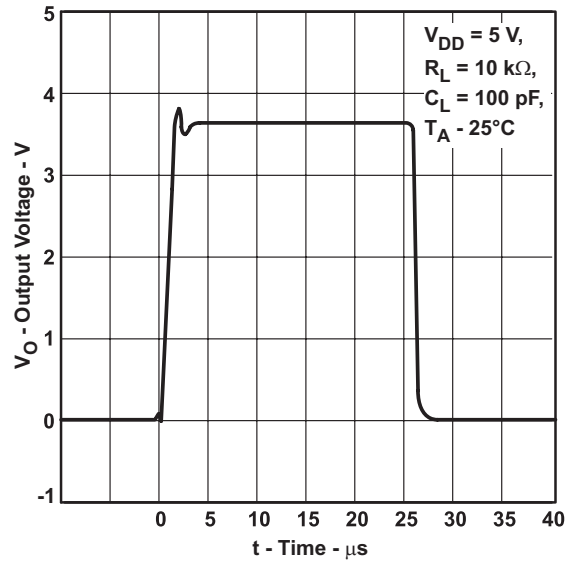


Figure 26.

**SLEW RATE
vs
SUPPLY VOLTAGE**

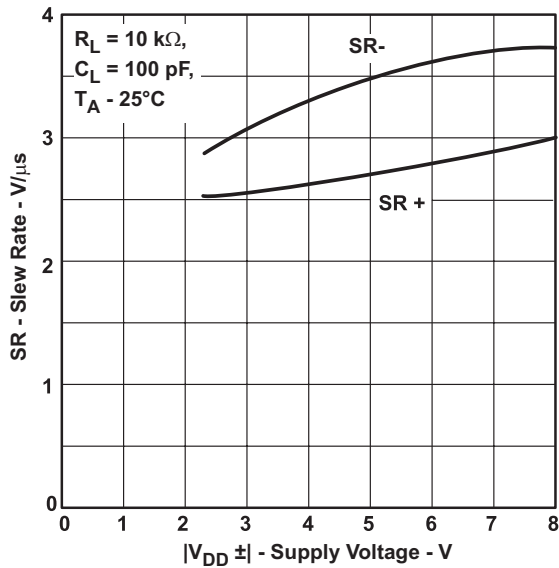


Figure 27.

**SLEW RATE
vs
FREE-AIR TEMPERATURE**

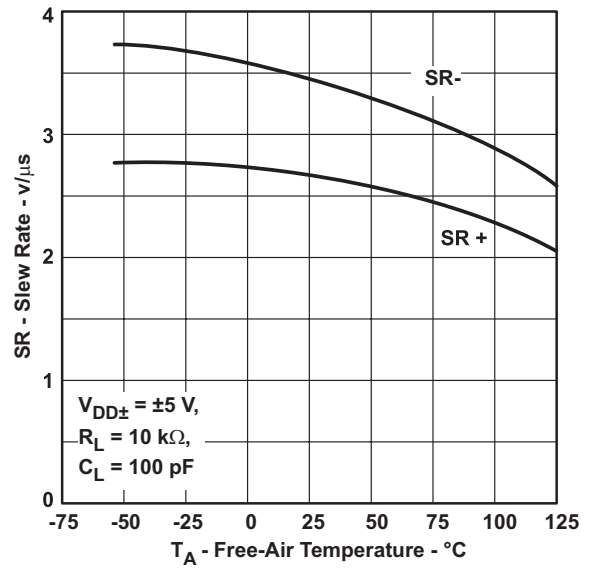


Figure 28.

TYPICAL CHARACTERISTICS (continued)

NOISE VOLTAGE
(REFERRED TO INPUT)
OVER A 10-SECOND INTERVAL

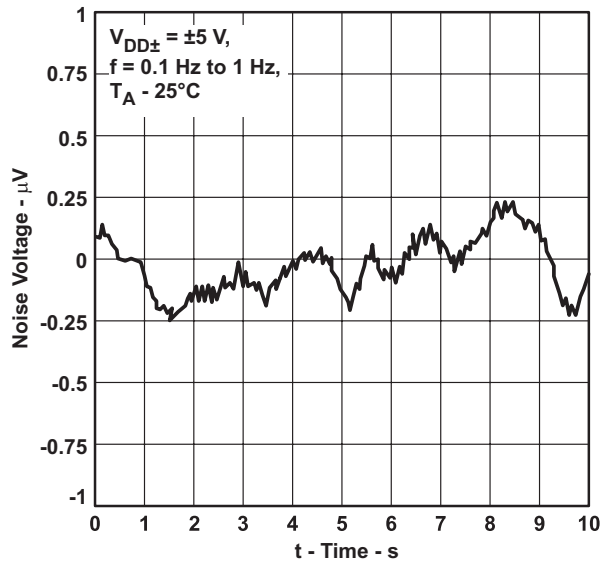


Figure 29.

NOISE VOLTAGE
(REFERRED TO INPUT)
OVER A 10-SECOND INTERVAL

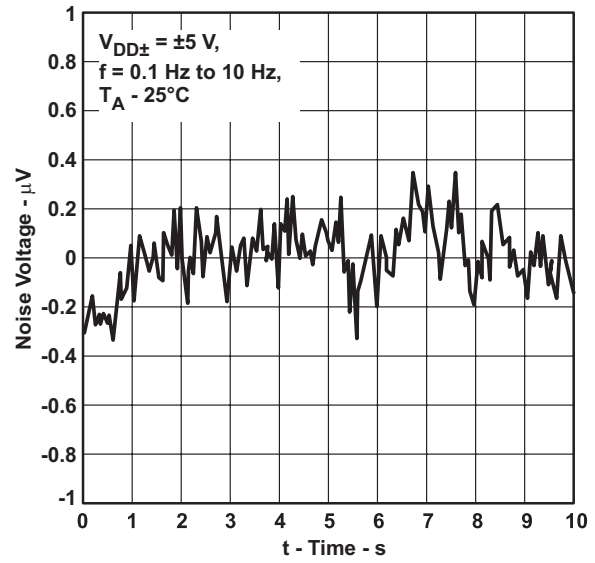


Figure 30.

GAIN-BANDWIDTH PRODUCT
vs
SUPPLY VOLTAGE

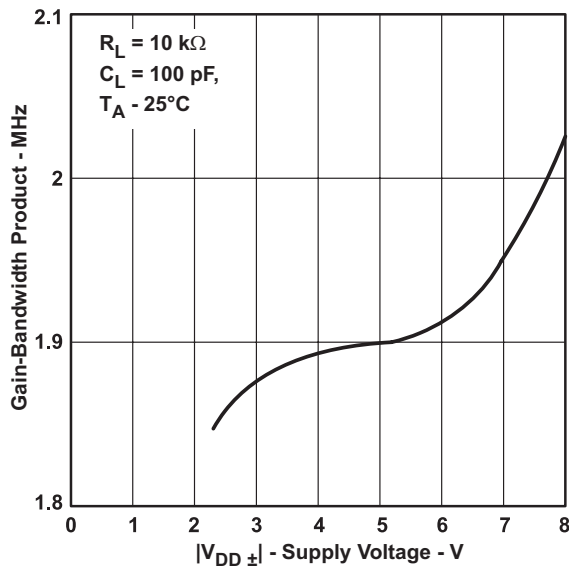


Figure 31.

GAIN-BANDWIDTH PRODUCT
vs
FREE-AIR TEMPERATURE

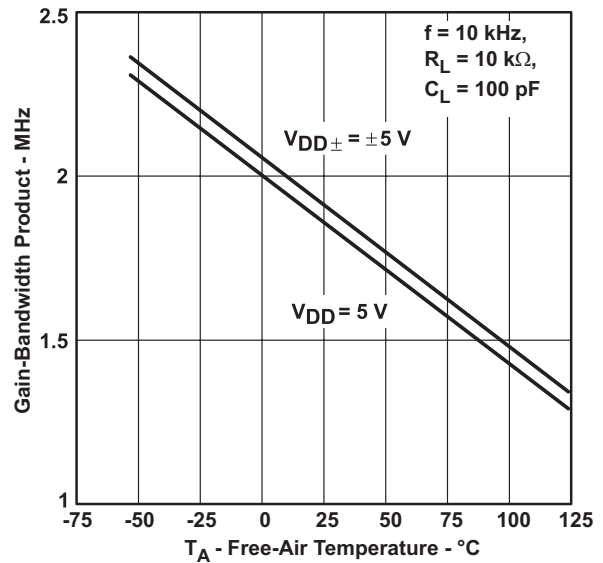
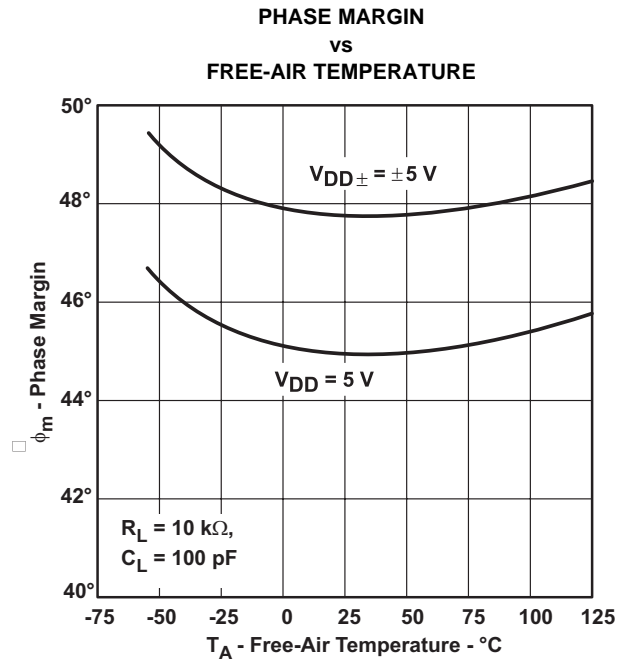
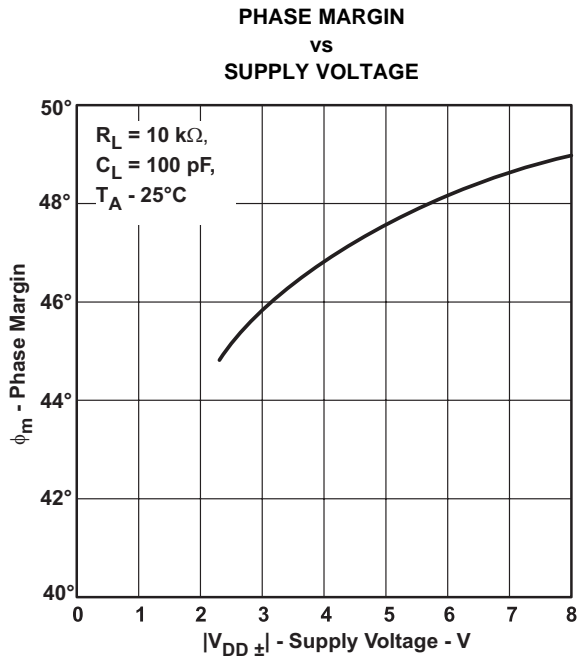


Figure 32.

TYPICAL CHARACTERISTICS (continued)



APPLICATION INFORMATION

LATCH-UP AVOIDANCE

Because CMOS devices are susceptible to latch-up due to their inherent parasitic thyristors, the TLC2201 inputs and outputs are designed to withstand –100-mA surge currents without sustaining latch-up; however, techniques reducing the chance of latch-up should be used whenever possible. Internal protection diodes should not be forward biased in normal operation. Applied input and output voltages should not exceed the supply voltage by more than 300 mV. Care should be exercised when using capacitive coupling on pulse generators. Supply transients should be shunted by the use of decoupling capacitors (0.1 μ F typical) located across the supply rails as close to the device as possible.

ELECTROSTATIC DISCHARGE PROTECTION

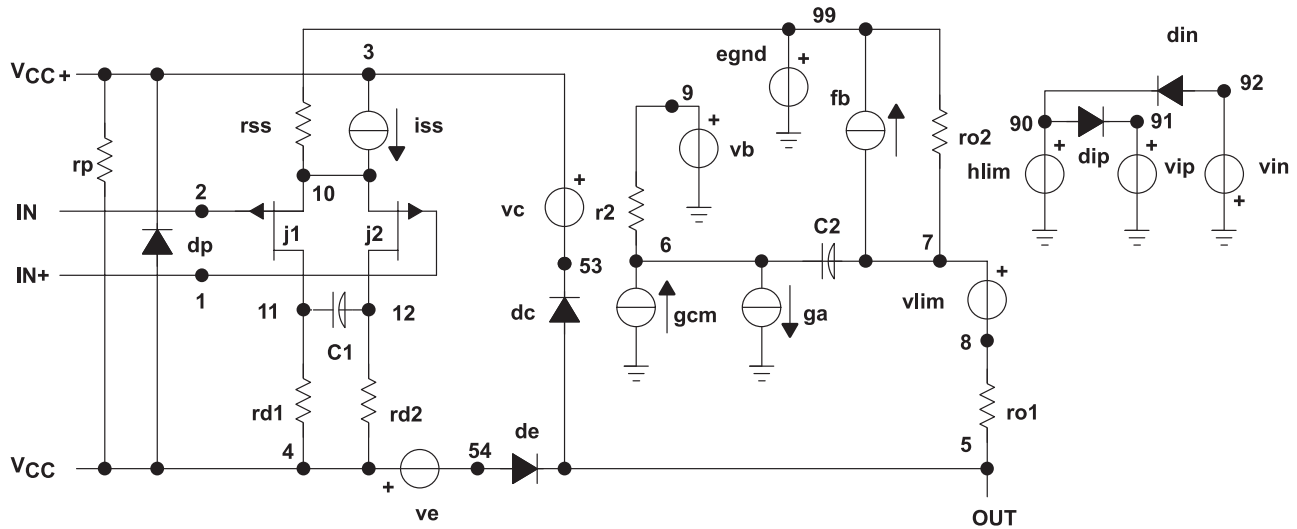
These devices use internal ESD-protection circuits that prevent functional failures at voltages at or below 2000 V. Care should be exercised in handling these devices as exposure to ESD may result in degradation of the device parametric performance.

MACROMODEL INFORMATION

Macromodel information provided was derived using Microsim Parts™, the model generation software used with Microsim PSpice™. The Boyle macromodel⁽³⁾ and subcircuit in [Figure 35](#) were generated using the TLC2201 typical electrical and operating characteristics at 25°C. Using this information, output simulations of the following key parameters can be generated to a tolerance of 20% (in most cases):

- Maximum positive output voltage swing
- Maximum negative output voltage swing
- Slew rate
- Quiescent power dissipation
- Input bias current
- Open-loop voltage amplification
- Unity-gain frequency
- Common-mode rejection ratio
- Phase margin
- DC output resistance
- AC output resistance
- Short-circuit output current limit

(3) G. R. Boyle, B. M. Cohn, D. O. Pederson, and J. E. Solomon, "Macromodeling of Integrated Circuit Operational Amplifiers", IEEE Journal of Solid-State Circuits, SC-9, 353 (1974).



```

.subckt TLC220x 1 2 3 4 5
*
c1 11 12 8.51E12
c2 6 7 50.00E12
cpsr 85 86 79.6E9
dcm+ 81 82 dx
dcm 83 81 dx
dc 5 53 dx
de 54 5 dx
dlp 90 91 dx
dln 92 90 dx
dp 4 3 dx
ecmr 84 99 (2,99) 1
egnd 99 0 poly(2) (3,0) (4,0) 0 .5 .5
epsr 85 0 poly(1) (3,4) 200E6 20E6
ense 89 2 poly(1) (88,0) 100E6 1
fb 7 99 poly(6) vb vc ve vlp vln
+ vpsr 0 + 895.9E3 90E3 90E3 90E3 90E3 895E3
ga 6 0 11 12 314.2E6
gcm 0 6 10 99 1.295E9
gpsr 85 86 (85,86) 100E6
grd1 60 11 (60,11) 3.141E4
grd2 60 12 (60,12) 3.141E4
hlim 90 0 vlim 1k
hcmr 80 1 poly(2) vcm+ vcm 0 1E2 1E2
irp 3 4 965E6

iss 3 10 dc 135.0E6
iio 2 0 .5E12
i1 88 0 1E21
j1 11 89 10 jx
j2 12 80 10 jx
r2 6 9 100.0E3
rcm 84 81 1k
rn1 88 0 1500
ro1 8 5 188
ro2 7 99 187
rss 10 99 1.481E6
vad 60 4 .3v
vcm+ 82 99 2.2
vcm 83 99 4.5
vb 9 0 dc 0
vc 3 53 dc .9
ve 54 4 dc .8
vlim 7 8 dc 0
vlp 91 0 dc 2.8
vln 0 92 dc 2.8
vpsr 0 86 dc 0
.model dx d(is=800.0E18)
.model jx pjf(is=500.0E15 beta=1.462E3
+ vto=.155 kf=1E17)
.endsx
    
```

Figure 35. Boyle Macromodel and Subcircuit

PACKAGING INFORMATION

| Orderable part number | Status (1) | Material type (2) | Package Pins | Package qty Carrier | RoHS (3) | Lead finish/ Ball material (4) | MSL rating/ Peak reflow (5) | Op temp (°C) | Part marking (6) |
|---------------------------------|---------------|----------------------|----------------|-----------------------|-------------|--------------------------------------|-----------------------------------|--------------|---|
| 5962-9088203V2A | Active | Production | LCCC (FK) 20 | 55 TUBE | No | SNPB | N/A for Pkg Type | -55 to 125 | 5962- 9088203V2A TLC2201 AMFKBQMLV |
| 5962-9088203V2A.A | Active | Production | LCCC (FK) 20 | 55 TUBE | No | SNPB | N/A for Pkg Type | -55 to 125 | 5962- 9088203V2A TLC2201 AMFKBQMLV |

⁽¹⁾ **Status:** For more details on status, see our [product life cycle](#).

⁽²⁾ **Material type:** When designated, preproduction parts are prototypes/experimental devices, and are not yet approved or released for full production. Testing and final process, including without limitation quality assurance, reliability performance testing, and/or process qualification, may not yet be complete, and this item is subject to further changes or possible discontinuation. If available for ordering, purchases will be subject to an additional waiver at checkout, and are intended for early internal evaluation purposes only. These items are sold without warranties of any kind.

⁽³⁾ **RoHS values:** Yes, No, RoHS Exempt. See the [TI RoHS Statement](#) for additional information and value definition.

⁽⁴⁾ **Lead finish/Ball material:** Parts may have multiple material finish options. Finish options are separated by a vertical ruled line. Lead finish/Ball material values may wrap to two lines if the finish value exceeds the maximum column width.

⁽⁵⁾ **MSL rating/Peak reflow:** The moisture sensitivity level ratings and peak solder (reflow) temperatures. In the event that a part has multiple moisture sensitivity ratings, only the lowest level per JEDEC standards is shown. Refer to the shipping label for the actual reflow temperature that will be used to mount the part to the printed circuit board.

⁽⁶⁾ **Part marking:** There may be an additional marking, which relates to the logo, the lot trace code information, or the environmental category of the part.

Multiple part markings will be inside parentheses. Only one part marking contained in parentheses and separated by a "~" will appear on a part. If a line is indented then it is a continuation of the previous line and the two combined represent the entire part marking for that device.

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OTHER QUALIFIED VERSIONS OF TLC2201-SP :

- Catalog : [TLC2201](#)
- Military : [TLC2201M](#)

NOTE: Qualified Version Definitions:

- Catalog - TI's standard catalog product
- Military - QML certified for Military and Defense Applications

TUBE


*All dimensions are nominal

| Device | Package Name | Package Type | Pins | SPQ | L (mm) | W (mm) | T (μm) | B (mm) |
|-------------------|--------------|--------------|------|-----|--------|--------|--------|--------|
| 5962-9088203V2A | FK | LCCC | 20 | 55 | 506.98 | 12.06 | 2030 | NA |
| 5962-9088203V2A.A | FK | LCCC | 20 | 55 | 506.98 | 12.06 | 2030 | NA |

GENERIC PACKAGE VIEW

FK 20

LCCC - 2.03 mm max height

8.89 x 8.89, 1.27 mm pitch

LEADLESS CERAMIC CHIP CARRIER

This image is a representation of the package family, actual package may vary.
Refer to the product data sheet for package details.



4229370VA\

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